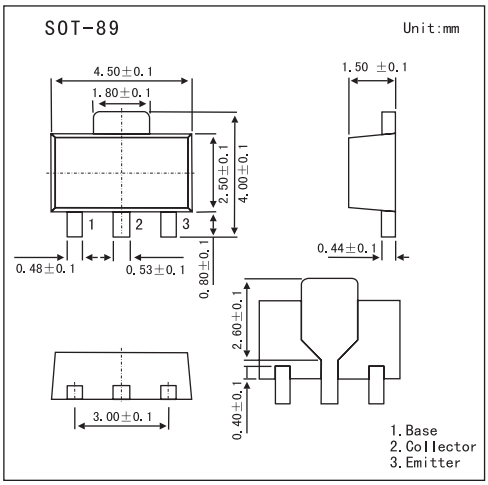
TY Semicondutor®

Product specification

2SC3651



■ Features

- High DC current gain
- High breakdown voltage
- Low colleotor-to- emitter saturation voltage
- High V_{EBO} (V_{EBO}≥15V)
- Very small size making it easy to provide high-density small-sized hybrid IC's.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
collector-base voltage	V_{CBO}	120	V
collector-emitter voltage	V_{CEO}	100	V
emitter-base voltage	V_{EBO}	15	V
collector current	I_C	200	mA
Collector Current (pulse)	I_{CP}	300	mA
Collector Dissipation	P_C	500	mA
		1.3 *	W
Junotion Temperature	T_J	150	℃
storage Temperature	T_{stg}	-55 to 150	℃

*Mounted on ceramic board (250mm^{2}X0.8mm)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
collector cutoff Current	I_{CBO}	V_{CB}=80V,I_E=0			0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=10V,I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=5V,I_C=10mA	500	1000	2000	
		V_{CE}=5V,I_C=100mA	400			
Gain-Bandwidth product	f_T	V_{CE}=10V,I_C=10mA		150		MHz
Output Capacitance	cob	V_{CB}=10V,f=1MHz		6.5		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA,I_B=2mA		0.15	0.5	V
Base to Emitter Stauration Voltage	$V_{BE(sat)}$	I_C=100mA,I_E=2mA				V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0				V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0				V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0				V

■ Marking

Marking	CG